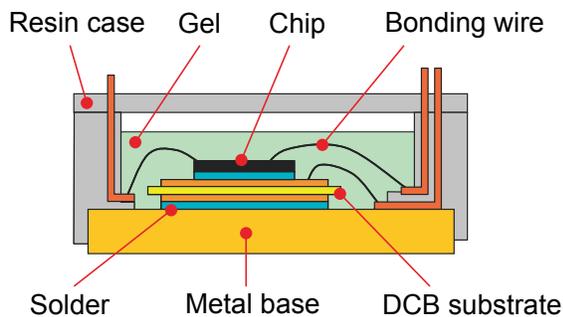


Fuji SiC Power Modules (Under Development)

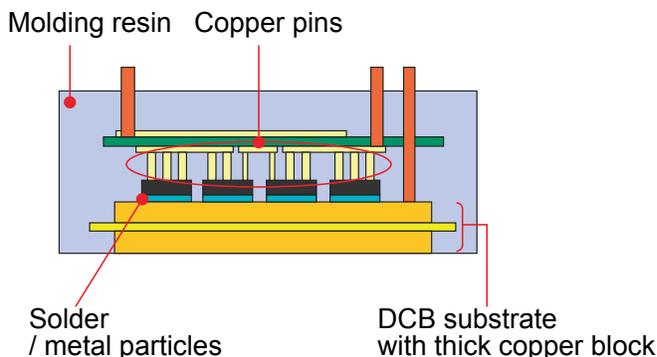
- **Low resistance device achieves smaller chip**
 - MOSFET: Epi-channel structure provides low resistance
 - SBD: Optimizing dopant concentration in epitaxial layer
- **New Packaging Technology**
 - 1/4 volume compared to conventional package
 - Wire-bonding-less connection
 - Low thermal impedance DCB substrate

Conventional package for Si device



Compact and High-capacity

New package for SiC device



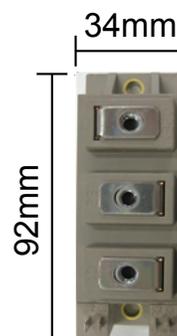
All SiC Module

2in1 / 1200V / 100A



Element development accelerated through joint development with National Institute of Advanced Industrial Science and Technology (AIST)

Si Module



All SiC Module

